www.omseni.com

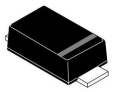
OM SENI

MBR120LSFT1G, MBR120LSFT3G
Surface Mount Schottky Power Rectifier

Plastic SOD−123 Package

This device uses the Schottky Barrier principle with a large area metal−to−silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package also provides an easy to work with alternative to leadless 34 package style. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC−DC and DC−DC converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 20 VOLTS



SOD−123FL CASE 498

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 125°C Operating Junction Temperature
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- ESD Rating:
  - Human Body Model = 3B
  - Machine Model = C
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics

- Device Marking: L2L
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MARKING DIAGRAM



L2L = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBR120LSFT1G	SOD−123FL (Pb−Free)	3,000 / Tape & Reel **
MBR120LSFT3G	SOD−123FL (Pb−Free)	10,000 / Tape & Reel ***

OM SENI

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	V
Average Rectified Forward Current (At Rated V_R, T_L = 115°C)	I_O	1.0	A
Peak Repetitive Forward Current (At Rated V_R, Square Wave, 100 kHz, T_L = 110°C)	I_{FRM}	2.0	A
Non−Repetitive Peak Surge Current (Non−Repetitive peak surge current, halfwave, single phase, 60 Hz)	I_{FSM}	50	A
Storage Temperature	T_{stg}	−55 to 150	°C
Operating Junction Temperature	T_J	−55 to 125	°C
Voltage Rate of Change (Rated V_R, T_J = 25°C)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance − Junction−to−Lead (Note 1) Thermal Resistance − Junction−to−Lead (Note 2) Thermal Resistance − Junction−to−Ambient (Note 1) Thermal Resistance − Junction−to−Ambient (Note 2)	R_{tjl} R_{tjl} R_{tja} R_{tja}	26 21 325 82	°C/W

1. Mounted with minimum recommended pad size, PC Board FR4.
2. Mounted with 1 in. copper pad (Cu area 700 mm^2).

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 3), See Figure 2	V_F	**T_J = 25°C**	**T_J = 85°C**	V
(I_F = 0.1 A) (I_F = 1.0 A) (I_F = 3.0 A)		0.34 0.45 0.65	0.26 0.415 0.67	
Maximum Instantaneous Reverse Current (Note 3), See Figure 4	I_R	**T_J = 25°C**	**T_J = 85°C**	mA
(V_R = 20 V) (V_R = 10 V)		0.40 0.10	25 18	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2%.

OM SENI

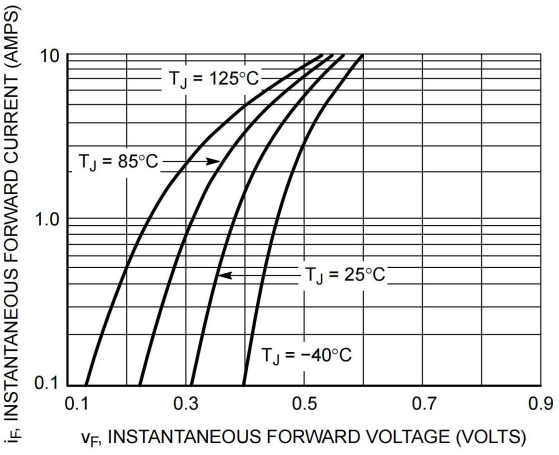


Figure 1. Typical Forward Voltage

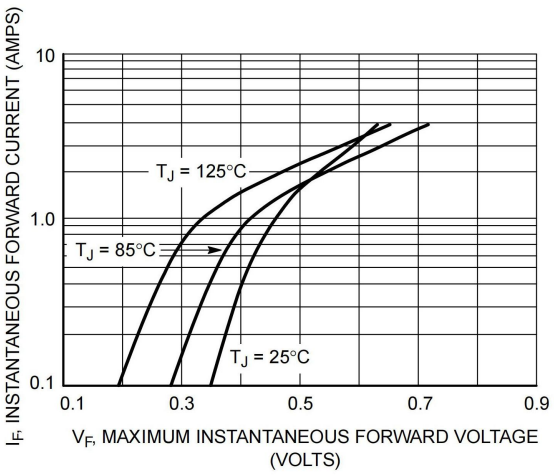


Figure 2. Maximum Forward Voltage

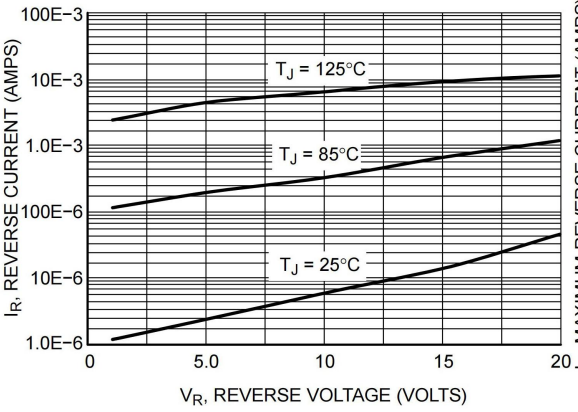


Figure 3. Typical Reverse Current

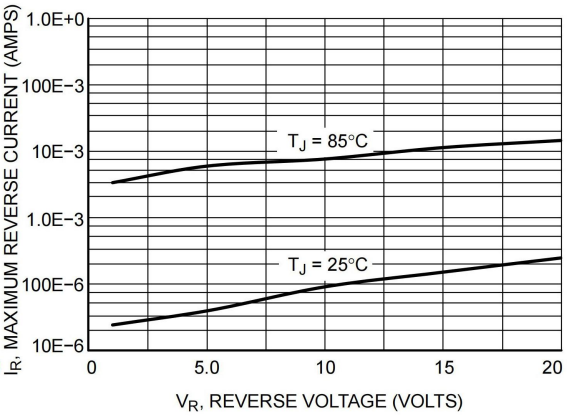


Figure 4. Maximum Reverse Current

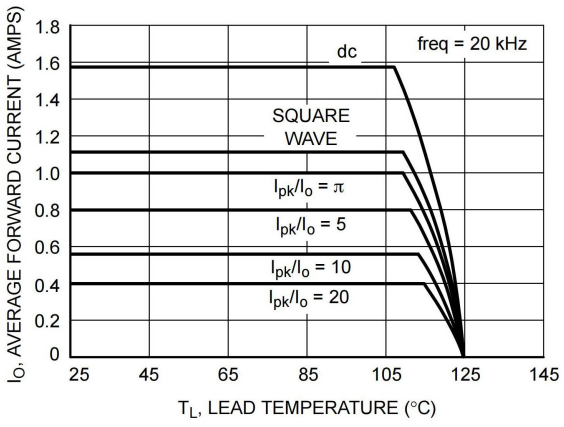


Figure 5. Current Derating

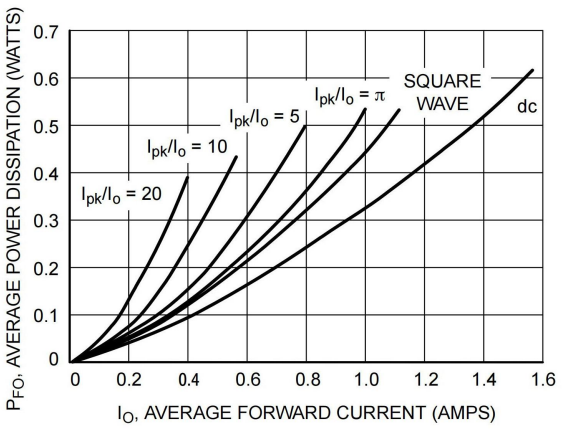


Figure 6. Forward Power Dissipation

OM SENI

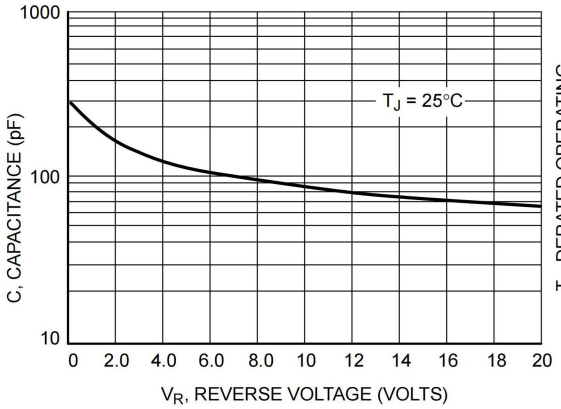


Figure 7. Capacitance

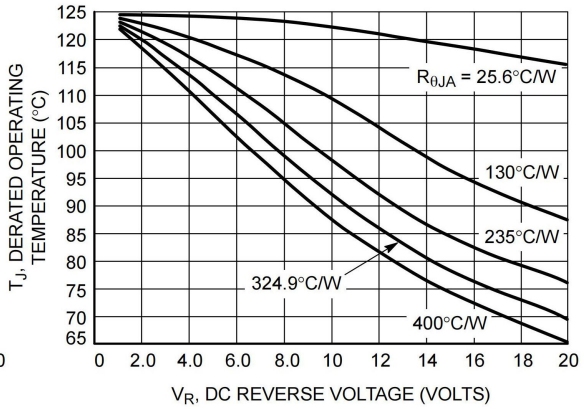


Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where
r(t) = thermal impedance under given conditions,
Pf = forward power dissipation, and
Pr = reverse power dissipation
This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

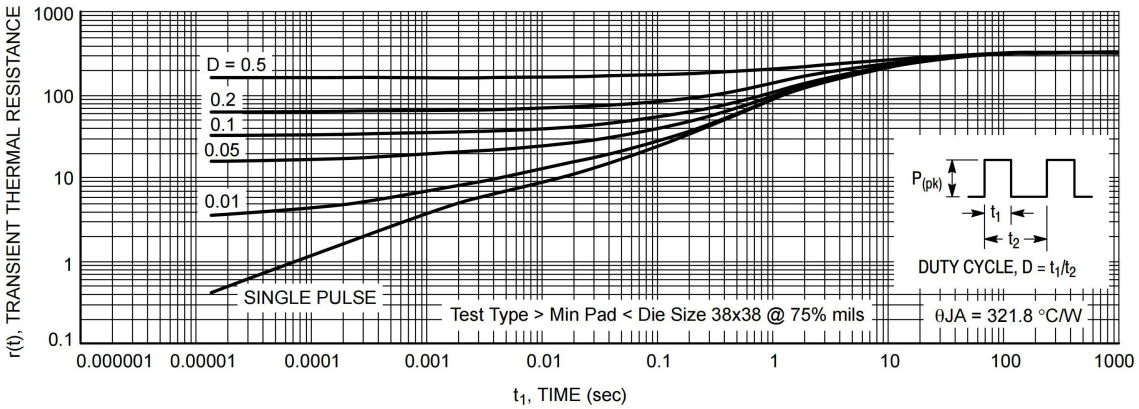


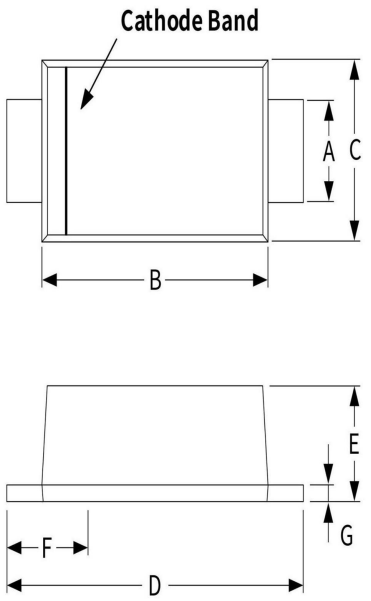
Figure 9. Thermal Response

OM SENI

Ordering Information

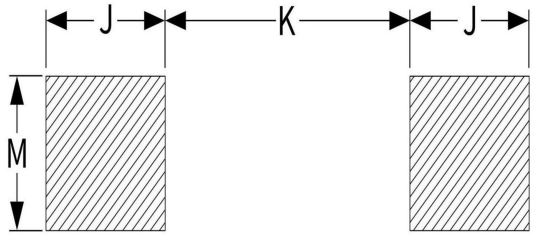
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOD-123FL	R1		3000	30000	240000	7"
SOD-123FL	R3		10000	40000	200000	13

Package Outline Dimensions (SOD -123FL)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.10	0.035	0.430
B	2.55	2.85	0.100	0.111
C	1.60	1.90	0.063	0.074
D	3.60	3.90	0.031	0.043
E	1.00	1.20	0.031	0.035
F	0.40	0.90	0.047	0.055
G	0.10	0.25	0.003	0.007

Suggested Pad Lavout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	1.00	-	0.040	-
K	-	1.90	-	0.074
M	1.50	-	0.059	-